

P- Channel 30-V (D-S) MOSFET

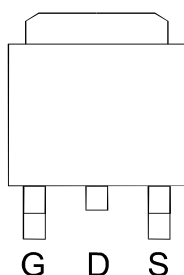
GENERAL DESCRIPTION

The ME25P03 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits , and low in-line power loss are needed in a very small outline surface mount package.

PIN CONFIGURATION

(TO-252-3L)

Top View

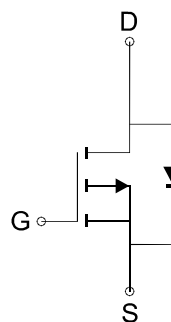


FEATURES

- $R_{DS(ON)} \leq 12m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} \leq 14.5m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

APPLICATIONS

- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter



P-Channel MOSFET

Ordering Information: ME25P03 (Pb-free)

ME25P03-G (Green product-Halogen free)

Absolute Maximum Ratings ($T_c = 25^\circ C$ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current*	$T_c = 25^\circ C$	I_D	-47	A
	$T_c = 70^\circ C$		-37	
Pulsed Drain Current		I_{DM}	-188	A
Maximum Power Dissipation*	$T_c = 25^\circ C$	P_D	42	W
	$T_c = 70^\circ C$		27	
Operating Junction Temperature		T_J	-55 to 150	$^\circ C$
Thermal Resistance-Junction to Case*		$R_{\theta JC}$	3	$^\circ C/W$

*The device mounted on 1in² FR4 board with 2 oz copper

DCC
正式發行

P- Channel 30-V (D-S) MOSFET

Electrical Characteristics (T_c =25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μ A	-1		-3	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} = $\pm$ 25V			$\pm$ 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	μ A
R _{DS(ON)}	Drain-Source On-State Resistance ^a	V _{GS} =-10V, I _D = -20A		9	12	m Ω
		V _{GS} =-4.5V, I _D = -16A		11	14.5	
V _{SD}	Diode Forward Voltage	I _S =-20A, V _{GS} =0V		-0.9	-1.2	V
DYNAMIC						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _D =-20A		55		nC
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-20A		28		
Q _{gs}	Gate-Source Charge			9.3		
Q _{gd}	Gate-Drain Charge			11.5		
C _{iss}	Input capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHz		2360		pF
C _{oss}	Output Capacitance			383		
C _{rss}	Reverse Transfer Capacitance			128		
t _{d(on)}	Turn-On Delay Time	V _{DS} =-15V, R _L =15 Ω V _{GEN} =-10V, R _G =3 Ω		43		ns
t _r	Turn-On Rise Time			18		
t _{d(off)}	Turn-Off Delay Time			134		
t _f	Turn-Off Fall Time			37		

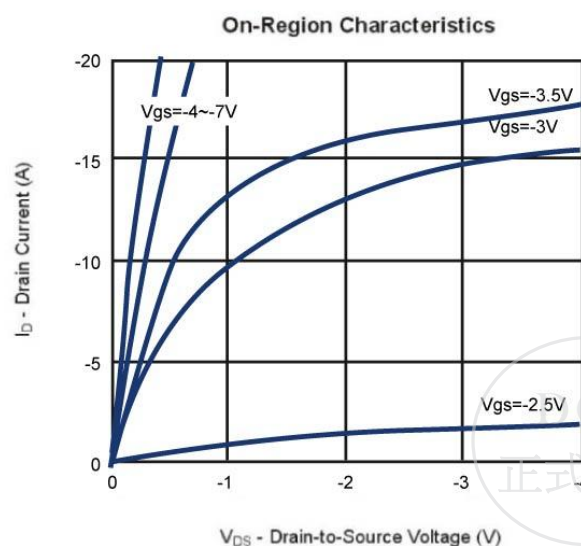
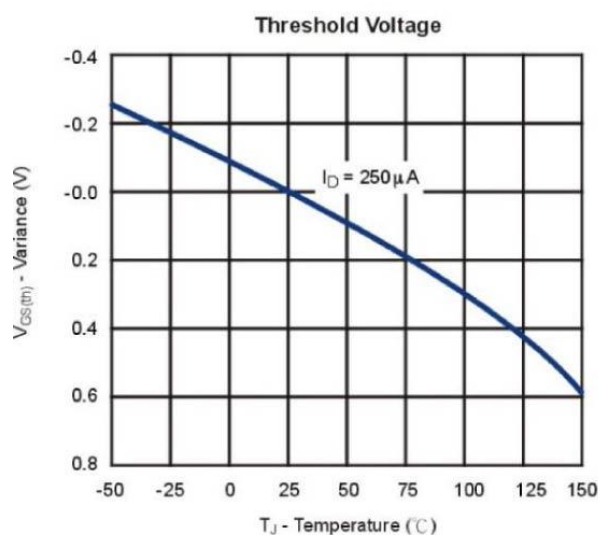
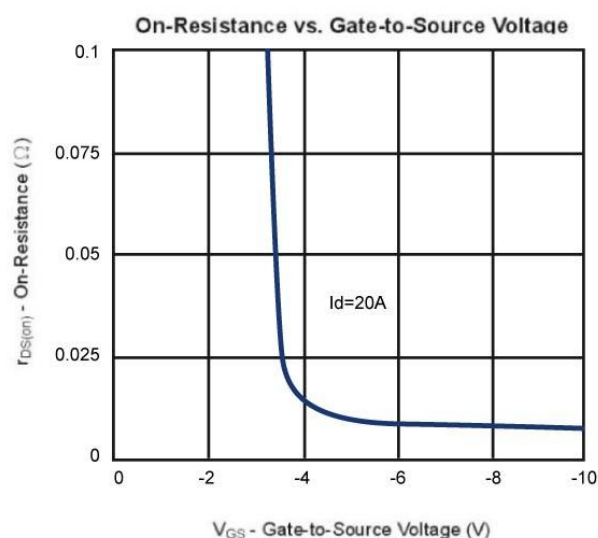
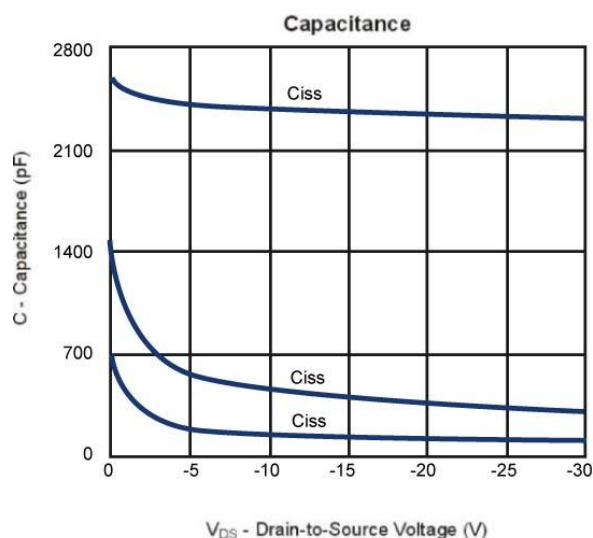
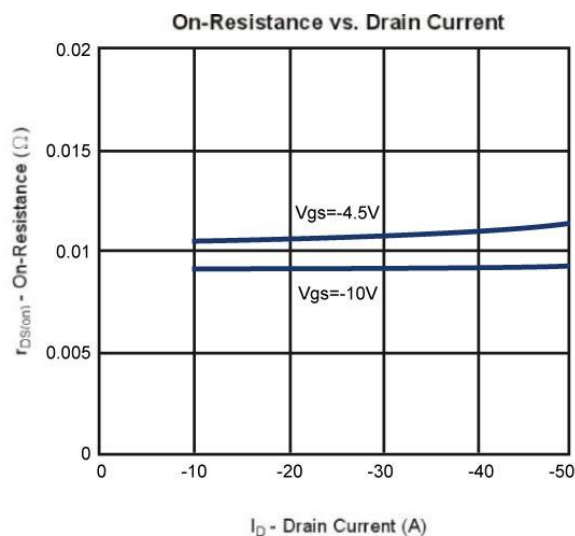
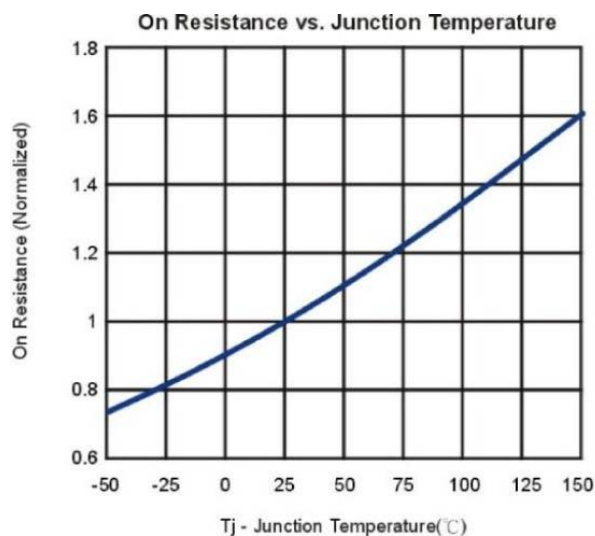
Notes: a. Pulse test: pulse width $\leq$ 300 μ s, duty cycle $\leq$ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.



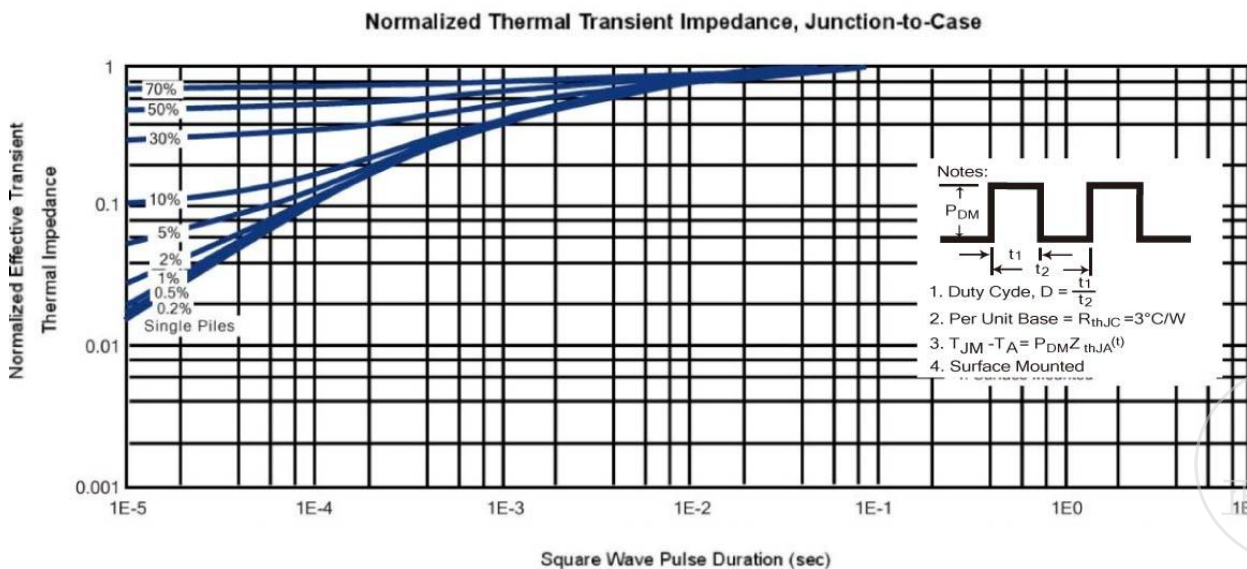
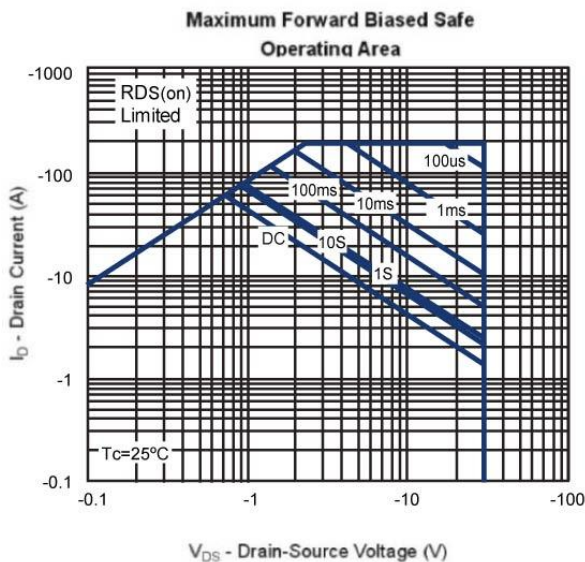
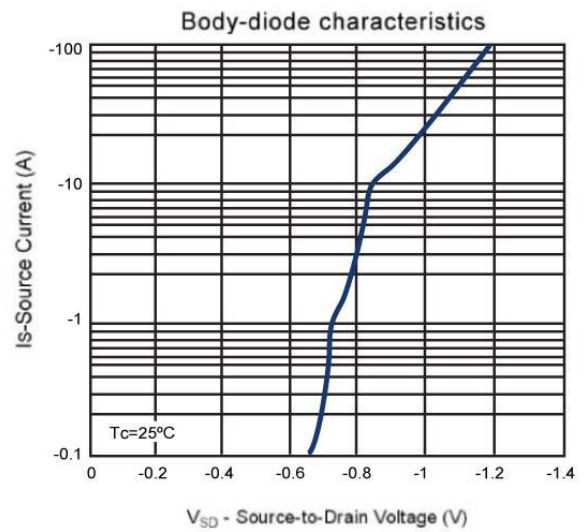
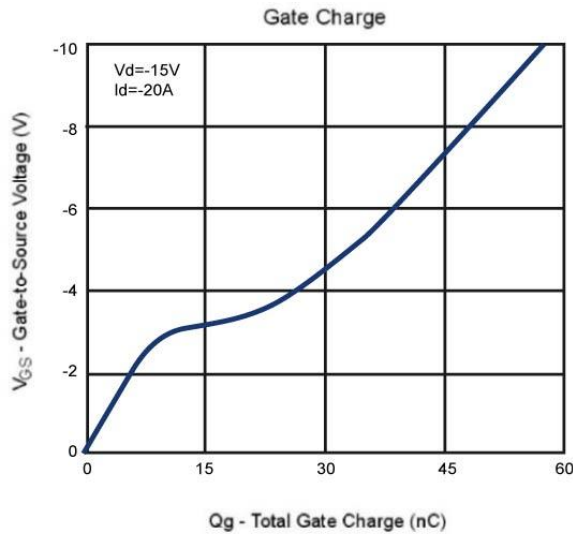
P- Channel 30-V (D-S) MOSFET

Typical Characteristics (T_J = 25°C Noted)

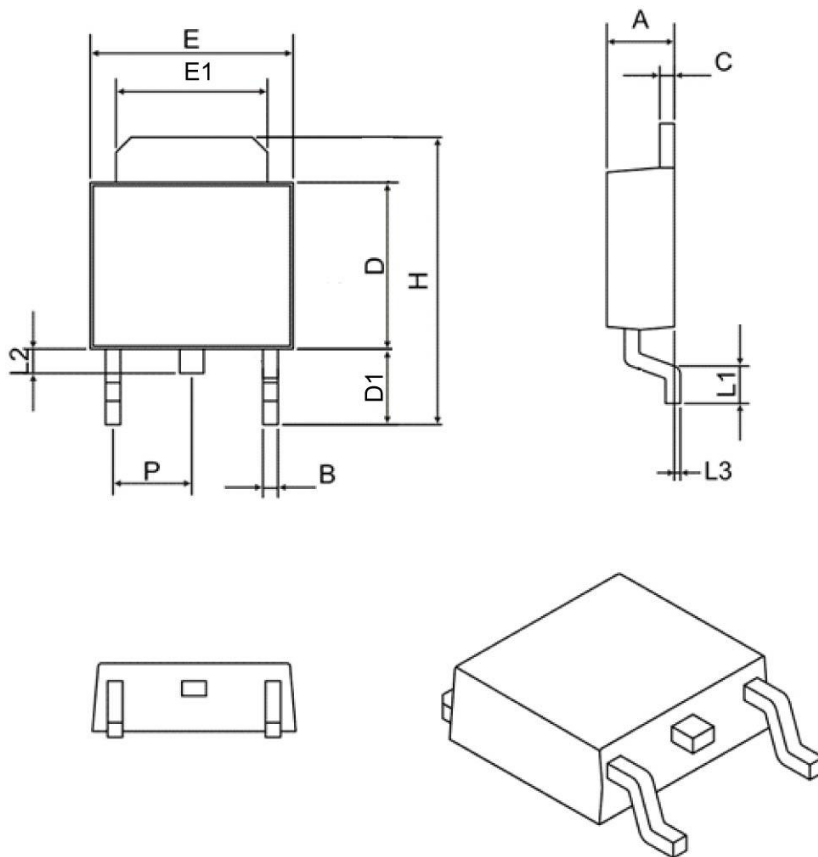


P- Channel 30-V (D-S) MOSFET

Typical Characteristics (T_J =25°C Noted)



TO252-3L Package Outline



SYMBOL	MIN	MAX
A	2.10	2.50
B	0.40	0.90
C	0.40	0.90
D	5.30	6.30
D1	2.20	2.90
E	6.30	6.75
E1	4.80	5.50
L1	0.90	1.80
L2	0.50	1.10
L3	0.00	0.20
H	8.90	10.40
P	2.30 BSC	

DCC
正式發行